

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	431695	(read adj only or read-only or rom) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/07/22 21:41
L2	10680	1 and select\$5 near3 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/07/22 21:42
L3	16	2 and common\$5 near3 layer with (drains or drain adj connections) with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/07/22 21:44
L4	1	3 and resistance with common\$5 near3 layer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/07/22 21:44
L5	99	2 and common\$5 near3 layer with (drains or drain adj connections)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/07/22 21:44
L6	5	5 and resistance with common\$5 near3 layer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/07/22 21:44

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(read-only adj memory and selection and transistors and electrode and drain and connection and common and layer and resistance and configuration).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/07/22 21:48